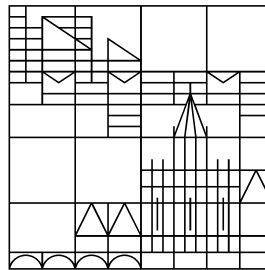


Seminar on the electronic properties of graphene

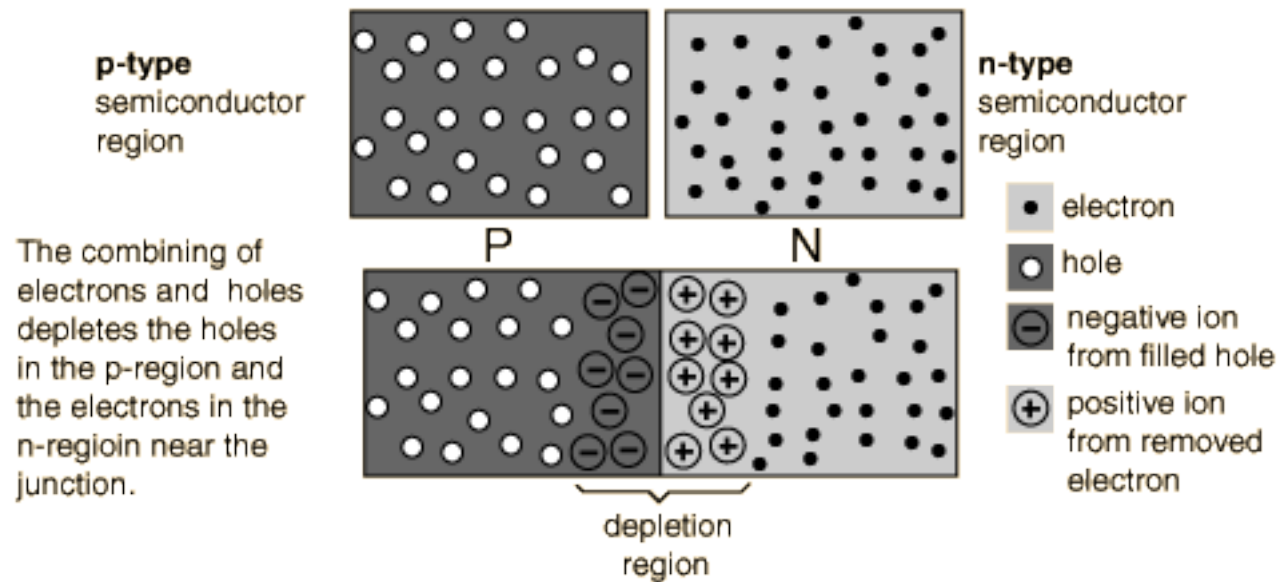
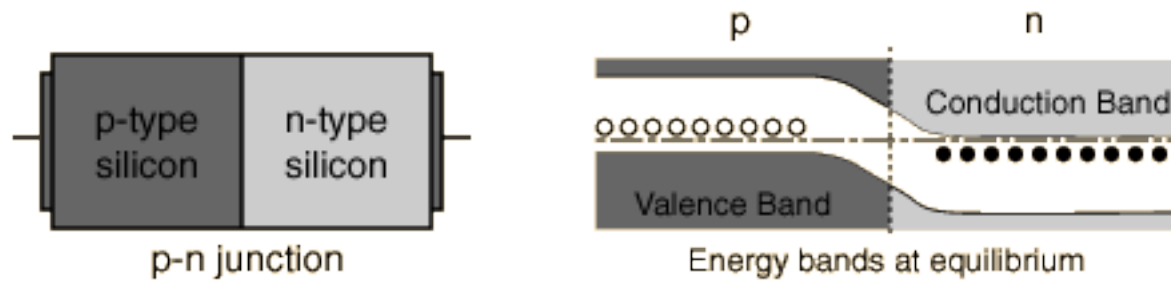
P-N Junctions in Graphene

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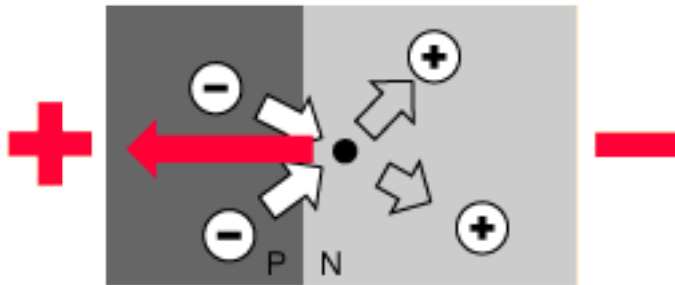


P-N junction in semiconductors



Applying a bias to a p-n junction

forward bias

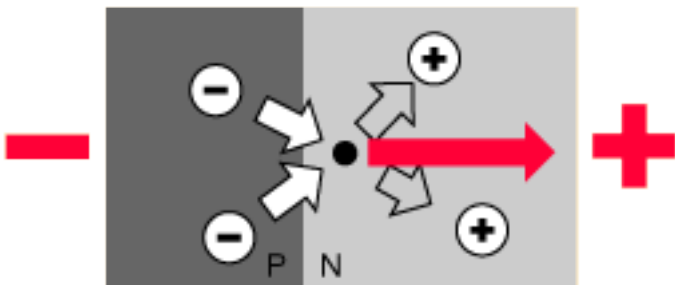


Force on electron from externally applied voltage.

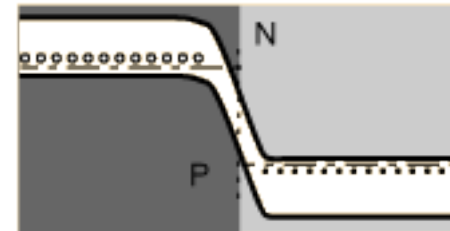
band structure for a forward bias



reverse bias

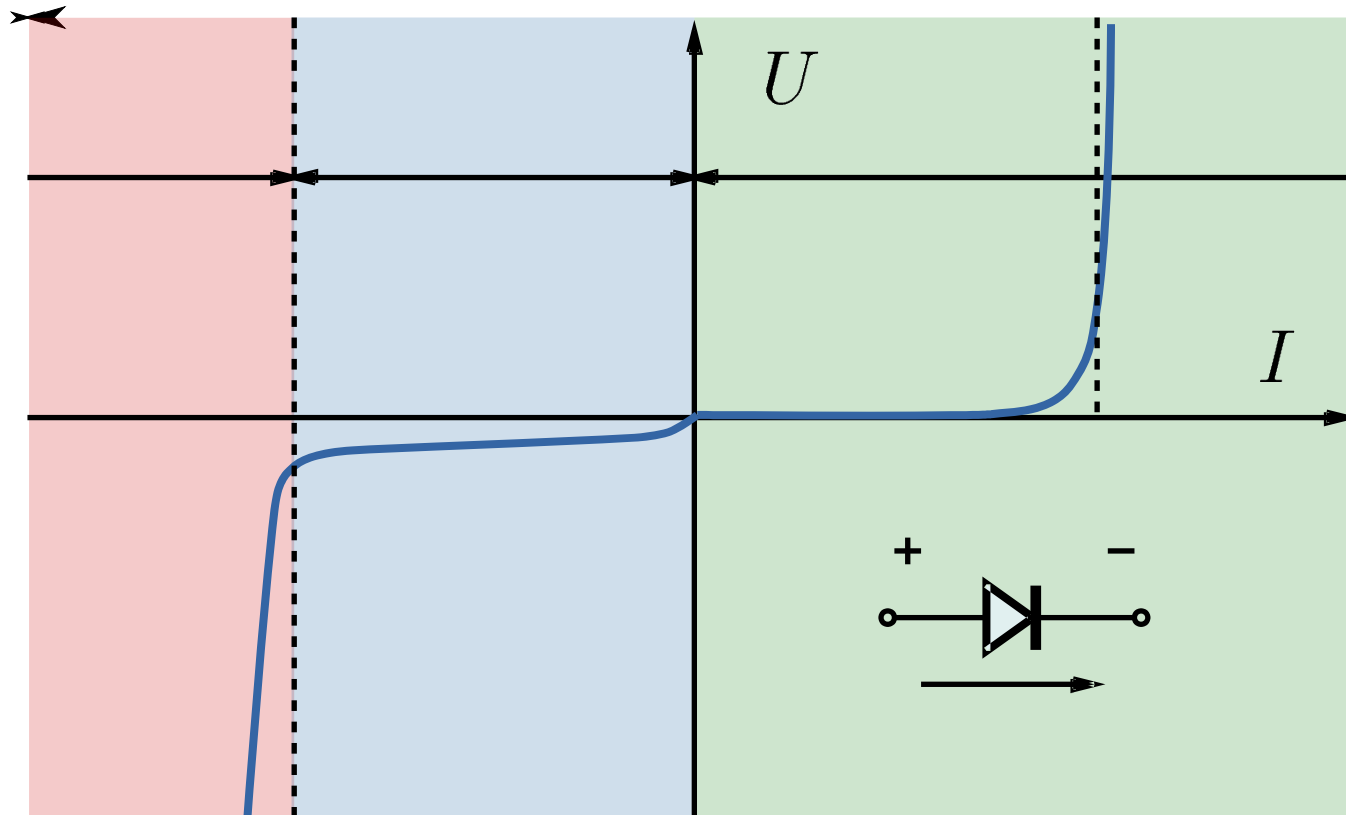


band structure for a reverse bias

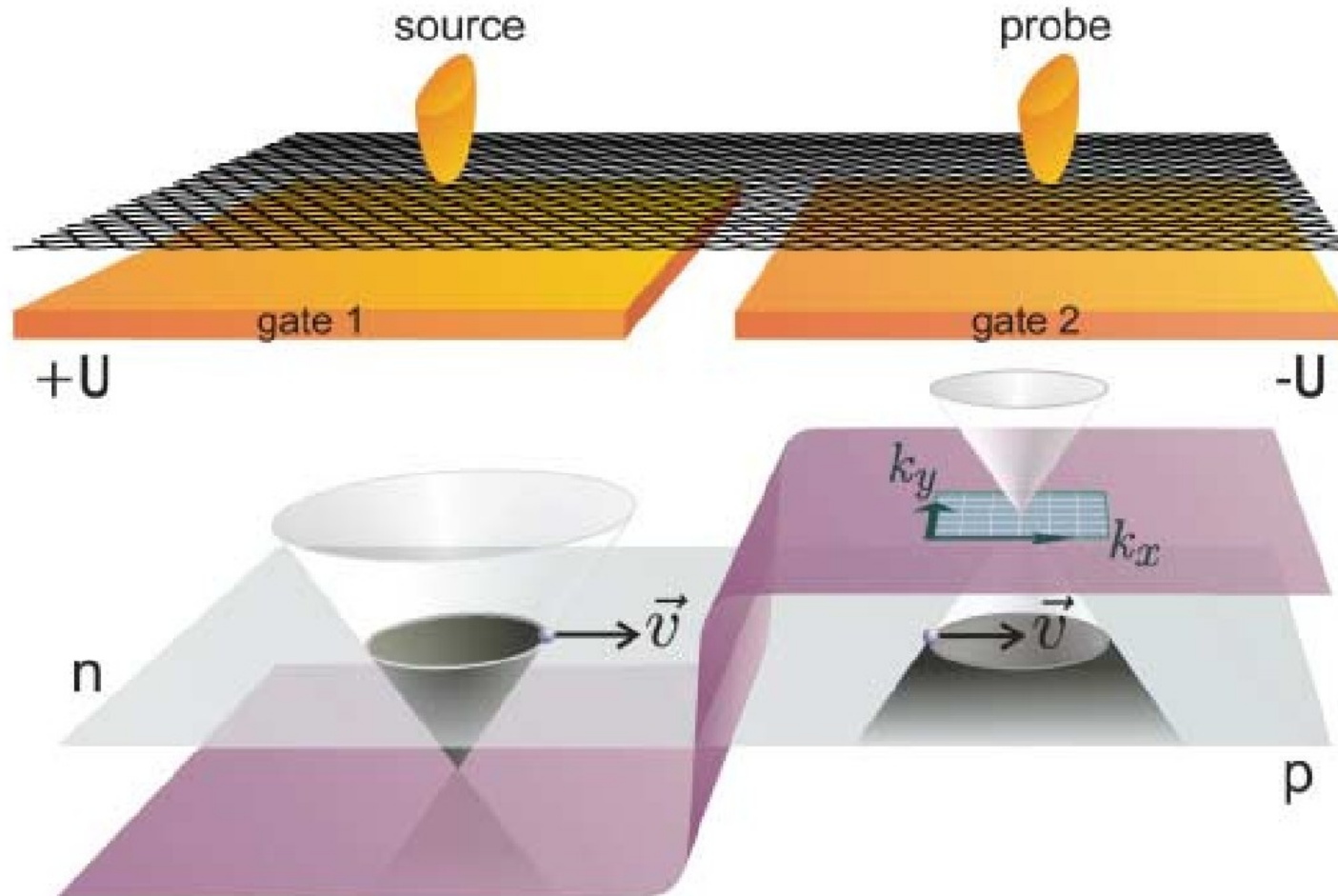


P-N junctions and solid state electronics

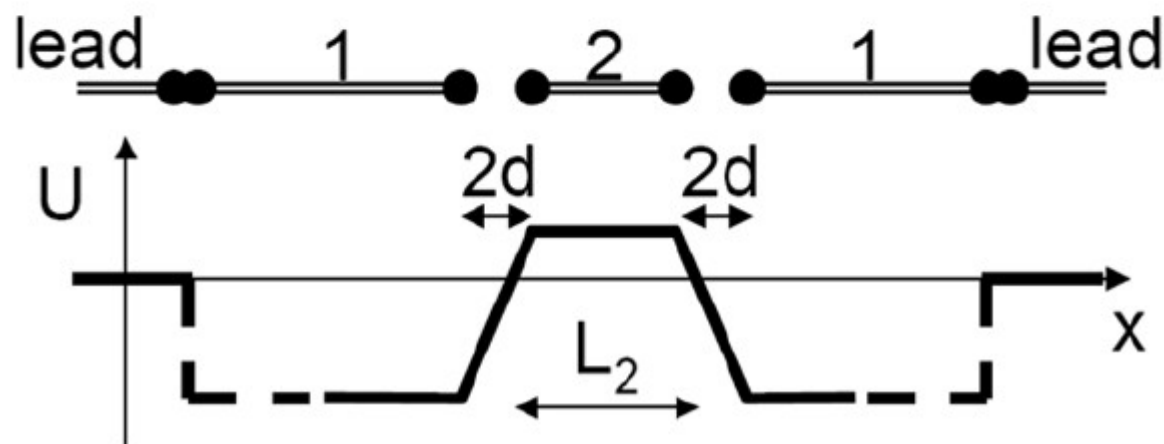
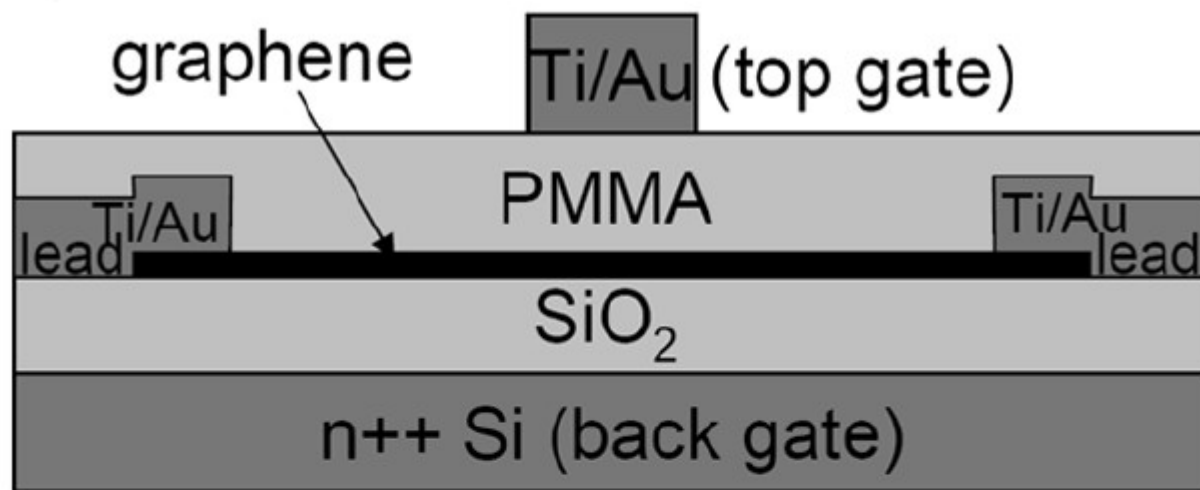
- diode



Realization of a P-N Junction in graphene



Realization of a P-N junction in graphene



Transport in a P-N junction for $B = 0$

Shytov *et al.*, arXiv:0708.3081
Cheianov *et al.*, *PRB* 74, 041403(R)

What is the probability T that a Dirac fermion tunnels through the P-N junction ?

- Massless Dirac Hamiltonian with a uniform electric field :

$$\mathcal{H} = \xi \boldsymbol{\sigma} \cdot \mathbf{p} + e\varphi(\mathbf{x})$$

- Electrostatic potential : $\varphi(\mathbf{x}) = -Ey$
- General form of the eigenstates : $\psi(t, \mathbf{x}) = e^{-i\varepsilon t + ip_x x} \psi(y)$

Transport in a P-N junction for $B = 0$

- Schrödinger equation in momentum representation :

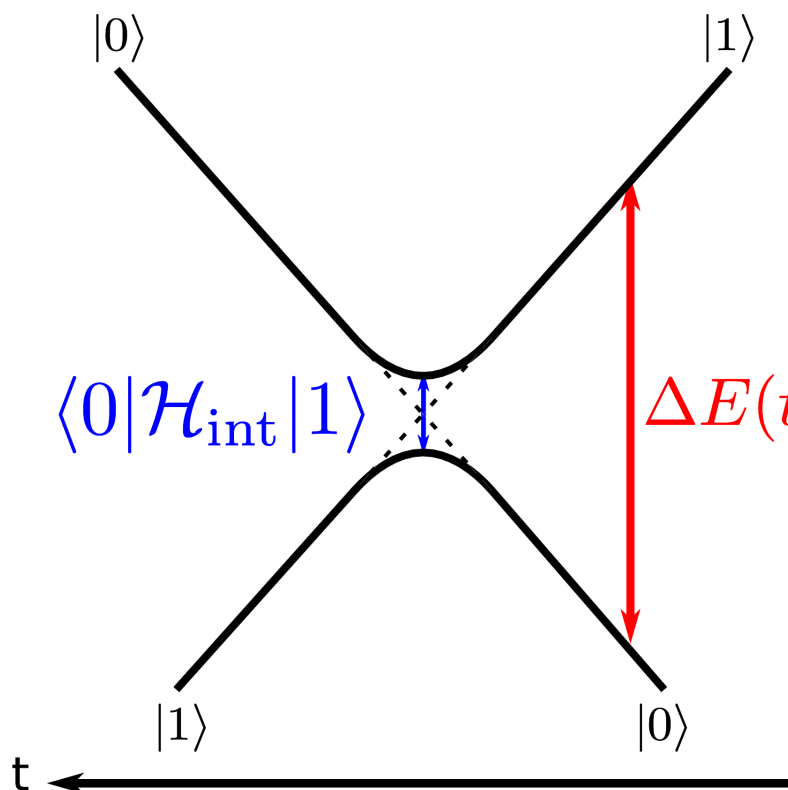
$$-ieE \frac{d\psi}{dp_y} = (\varepsilon - v_F(\sigma_x p_x + \sigma_y p_y))\psi$$

- Mapping to the Landau-Zener-Stückelberg problem :

$$\begin{cases} eE \rightarrow \hbar \\ p_y \rightarrow t \\ \varepsilon - v_F(\sigma_x p_x + \sigma_y p_y) \rightarrow \tilde{\mathcal{H}} \end{cases}$$

The Landau-Zener-Stückelberg problem

- Two level system with Hamiltonian : $\mathcal{H} = \mathcal{H}_0(t) + \mathcal{H}_{\text{int}}$



L. D. Landau, Phys. Z. 2, 46 (1932)

C. Zener, Proc. R. Soc. London A 137 696 (1932)

E. C. G. Stückelberg, Helv. Phys. Acta 5, 370 (1932)

- Result : $P_{0 \rightarrow 1} = 1 - P_{0 \rightarrow 0} = 1 - \exp\left(-2\pi \frac{|\langle 0 | \mathcal{H}_{\text{int}} | 1 \rangle|^2}{\alpha \hbar}\right)$

Transport in a P-N junction for $B = 0$

- Mapping of the Landau-Zener-Stückelberg result to the Dirac problem

$$\begin{cases} P_{0 \rightarrow 1} \rightarrow R \\ P_{0 \rightarrow 0} \rightarrow T \end{cases}$$

- The transmission coefficient is

$$T(p_x) = e^{\frac{-\pi \hbar v_F p_x^2}{|eE|}}$$

Transport in a P-N junction for $B \neq 0$

- We write the Dirac equation in the covariant form

$$\gamma^\mu (p_\mu - a_\mu) \psi = 0$$

$$\left\{ \begin{array}{l} \gamma^\mu = (\sigma_3, -i\sigma_2, -i\sigma_1) \\ x_\mu = (v_F t, x_1, x_2) \\ p_\mu = \hbar \left(\frac{i}{v_F} \partial_t, -i\partial_x, -i\partial_y \right) \\ a_\mu = \left(-\frac{e}{v_F} E y, -\frac{e}{c} B x, 0 \right) \end{array} \right.$$

- The Dirac equation is Lorentz invariant !

Is there a frame where $B = 0$?

A little bit of special relativity

- Lorentz invariants
$$\begin{cases} F_{\mu\nu}F^{\mu\nu} = 2(c^2 B^2 - E^2) \\ \varepsilon^{\mu\nu\rho\sigma} F_{\mu\nu}F_{\rho\sigma} = -4c(\mathbf{E} \cdot \mathbf{B}) \end{cases}$$

In our problem $\mathbf{E} \cdot \mathbf{B} = 0 = \mathbf{E}' \cdot \mathbf{B}' \Rightarrow \mathbf{B}' = 0$ is possible !

- Transformation of the electromagnetic field

$$\begin{cases} \mathbf{E}'_{\parallel} = \mathbf{E}_{\parallel} \\ \mathbf{E}'_{\perp} = \gamma(\mathbf{E}_{\perp} + c\boldsymbol{\beta} \wedge \mathbf{B}) \end{cases} \quad \begin{cases} \mathbf{B}'_{\parallel} = \mathbf{B}_{\parallel} \\ \mathbf{B}'_{\perp} = \gamma(\mathbf{B}_{\perp} - \frac{1}{c}\boldsymbol{\beta} \wedge \mathbf{E}) \end{cases}$$

In our case :

$$E'_y = \frac{E_y}{\gamma}$$

$$\beta_x = c \frac{B_z}{E}$$

Transport in a P-N junction for $B \neq 0$

- Hum... we are in a solid state device not in the vacuum : $c \rightarrow \frac{v_F}{c}$
- Is the transformation always possible ?

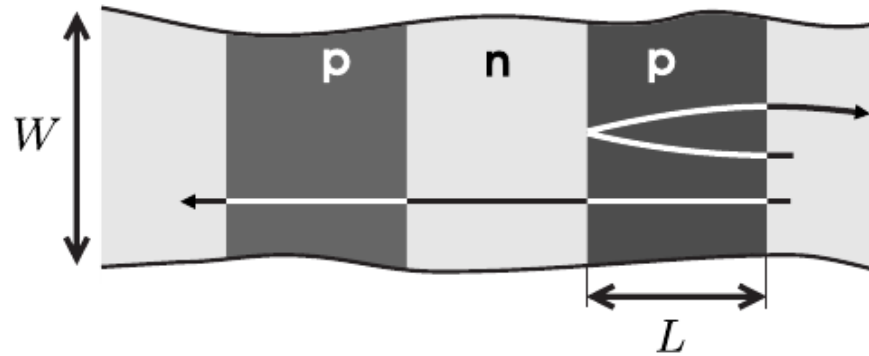
$$0 \leq \beta_x = \frac{v_F}{c} \frac{B}{E} \leq 1 \quad \Rightarrow \quad B \leq \frac{c}{v_F} E (\equiv B^*)$$

- In the new frame the transmission coefficient is : $T' = e^{\frac{-\pi \hbar v_F p'_1}{|eE'|}}$
- T is a scalar with respect to a Lorentz transformation.

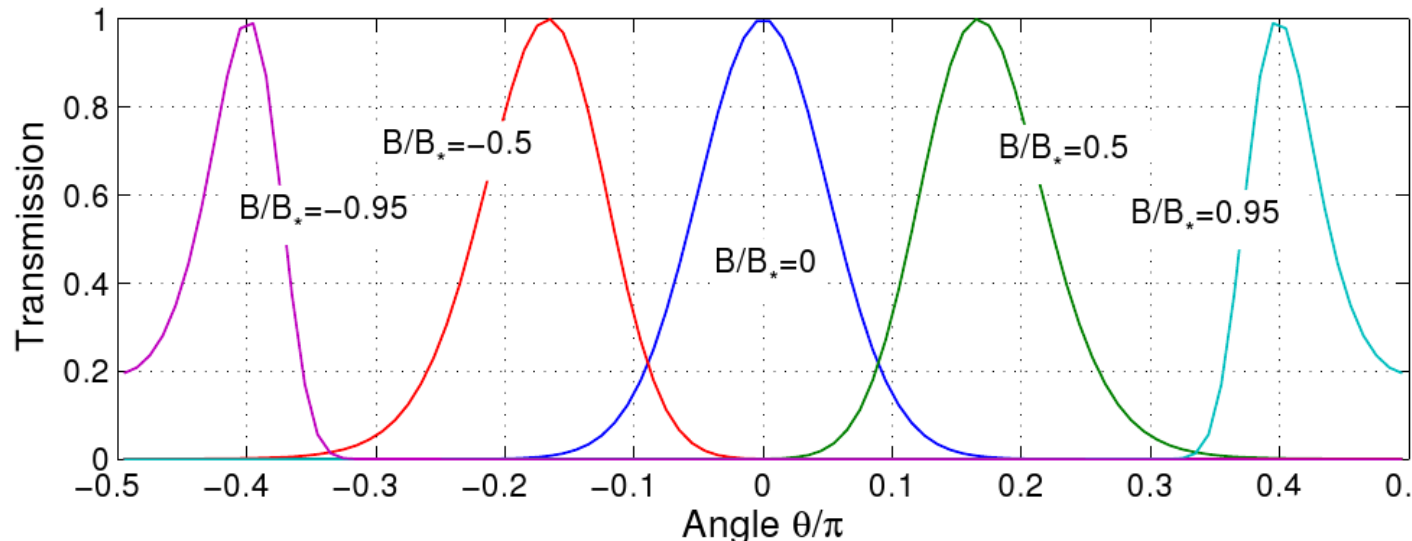
$$T(p_x, B) = e^{-\pi \frac{1}{\left(1 - \frac{v_F}{c} \frac{B}{E}\right)^{\frac{3}{2}}} \frac{\hbar v_F}{|eE|} \left(p_x + \frac{\varepsilon}{c} \frac{B}{E}\right)^2}$$

Transport in a P-N junction for $B \neq 0$

- Suppression of the tunneling with a B field possible except for $p_x = -\beta\varepsilon$



$$T(\theta) = e^{-\alpha\gamma^3 \left(\sin(\theta) - \frac{B}{B_*}\right)^2}$$



Conductance in a P-N junction

- Conductance is given by Landauer formula

$$G = \frac{e^2}{h} \sum_{-k_F < p_x < k_F} T(p_x) = \frac{we^2}{2\pi h} \int_{-k_F}^{k_F} dp_x T(p_x)$$

- We can extend the integration range to $\pm\infty$ (T vanishes extremely fast)
- We assume $\frac{\lambda_F}{2\pi} \ll d \ll w$

$$G(B \leq B^*) = \frac{e^2}{2\pi h} \frac{w}{d} \left(1 - \left(\frac{B}{B^*} \right)^2 \right)^{\frac{3}{4}}$$

Graphene P-N junctions in spintronics

- Graphene quantum dots

